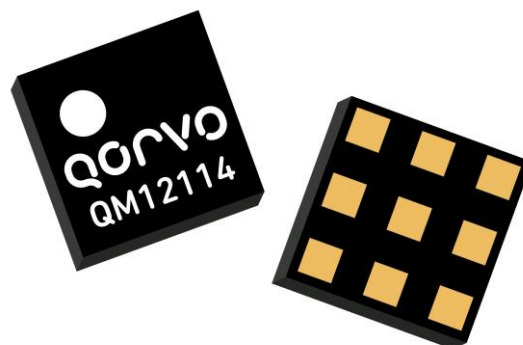


# QM12114 SP4T RFFE GSM HIGH POWER SWITCH

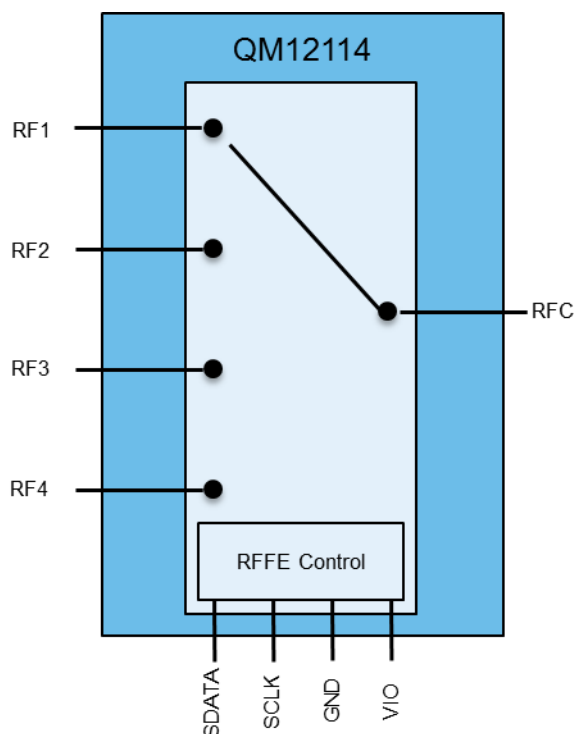
## Product Description

The QM12114 is a low loss, high isolation SP4T switch with performance optimized for GSM, CDMA, WCDMA, & LTE applications requiring high linearity and high power handling. The QM12114 is packaged in a compact 1.1mm x 1.1mm, 9-pin module which allows for a small solution size with no need for external DC blocking capacitors (when no external DC is applied to the device ports).



9 Pin 1.1 x 1.1 x 0.44 mm Package

## Functional Block Diagram



## Feature Overview

- Low Insertion Loss
- High Port-to-Port Isolation
- RFFE 2.0 compatible (52MHz Write Speed)
- Capable of 1.8V operation
- HBM Rating > 1kV on all ports
- Compact size: 1.1mm x 1.1mm x 0.44mm
- DC blocking capacitors are not required in typical applications

## Applications

- Cellular Handset Applications
- Cellular Modems and USB Devices
- Multi-Mode GSM, EDGE, WCDMA, and LTE Applications

## Ordering Information

PART NO.	DESCRIPTION
QM12114SB	5-pc Sample Bag
QM12114SR	100-pc, 7" Reel
QM12114TR13-5K	5000-pc, 13" Reel
QM12114DK	Fully Assembled Evaluation Kit

# QM12114

## SP4T RFFE GSM HIGH POWER SWITCH

### Absolute Maximum Ratings

PARAMETER	RATING
Storage Temperature	-65 to +150 °C
Operating Temperature	-30 to +90 °C
V <sub>IO</sub>	2.5 V
SDATA, SCLK	2.5 V
Maximum Power Handling	39 dBm, 1:1 VSWR, +25°C, 25% duty cycle

Operation of this device outside the parameter ranges given above may cause permanent damage.

### Recommended Operating Conditions

PARAMETER	MIN.	TYP.	MAX.	UNITS
V <sub>IO</sub> Supply Voltage	1.65	1.8	1.95	V
V <sub>IO</sub> Supply Current (Active Mode)		30		μA
V <sub>IO</sub> Supply Current (Low Power Mode)		3		μA
SDATA, SCLK Logic Low (Input)	0.00	0.00	0.3 x V <sub>IO</sub>	V
SDATA, SCLK Logic High (Input)	0.7 x V <sub>IO</sub>	1.8	V <sub>IO</sub>	V
SDATA Logic Low (Output)	0.00	0.00	0.2 x V <sub>IO</sub>	V
SDATA Logic High (Output)	0.8 x V <sub>IO</sub>	1.8	V <sub>IO</sub>	V
SDATA, SCLK Logic High Current		0.1	5	μA
Turn-On Time			20	μs
Switching Speed (50% of rising edge of last SCLK to 90% RF)		2	2.7	μs

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

# QM12114

## SP4T RFFE GSM HIGH POWER SWITCH

### Electrical Specifications

Test conditions unless otherwise stated: all unused RF ports terminated in 50Ω, Input and Output = 50Ω, T = 25°C, V<sub>IO</sub> = 1.8V, SDATA/SCLK = 1.8 V / 0 V

PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNITS
<b>Frequency Range</b>		698		6000	MHz
<b>Insertion Loss</b>					
RF1/2/3/4 to RFCOM	698 MHz to 960 MHz		0.23		dB
RF1/2/3/4 to RFCOM	1700 MHz to 2200 MHz		0.32		dB
RF1/2/3/4 to RFCOM	2300 MHz to 2700 MHz		0.35		dB
RF1/2/3/4 to RFCOM*	3300 MHz to 4200 MHz		0.44		dB
RF1/2/3/4 to RFCOM*	4400 MHz to 5000 MHz		0.60		dB
RF1/2/3/4 to RFCOM*	5000 MHz to 6000 MHz		0.60		dB
<b>Isolation</b>					
Port to Port	Refer to Isolation Matrix				
Port to RFCOM	Refer to Isolation Matrix				
<b>Harmonics</b>					
3Fo (B17)	fo = 704MHz; P <sub>in</sub> = 25dBm; CW		-88		dBm
2Fo (B13)	fo = 786.5MHz; P <sub>in</sub> = 25dBm; CW		-90		dBm
2Fo (B8)	fo = 897.5MHz; P <sub>in</sub> = 25dBm; CW		-99		dBm
2Fo (GSM 850/900)	fo = 824 – 915MHz; Pin = 35dBm; CW		-69		dBm
3Fo (GSM 850/900)	fo = 824 – 915MHz; Pin = 35dBm; CW		-56		dBm
≥ 4Fo - 12.75GHz (GSM 850/900)	fo = 824 – 915MHz; Pin = 35dBm; CW		-94		dBm
2Fo (GSM DCS/PCS)	fo = 1710 – 1980MHz; Pin = 32dBm; CW		-72		dBm
3Fo (GSM DCS/PCS)	fo = 1710 – 1980MHz; Pin = 32dBm; CW		-62		dBm
≥ 4Fo - 12.75GHz (GSM DCS/PCS)	fo = 1710 – 1980MHz; Pin = 32dBm; CW		-102		dBm
<b>IMD2</b>	F <sub>tx</sub> = 20dBm; F <sub>int</sub> = -15dBm				
Band VIII	F <sub>tx</sub> = 880 MHz, F <sub>int</sub> = 1805 MHz, F <sub>meas</sub> = 925 MHz, Measure on all Pins		-123		dBm
Band II	F <sub>tx</sub> = 1880 MHz, F <sub>int</sub> = 3840 MHz, F <sub>meas</sub> = 1960 MHz, Measure on all Pins		-121		dBm
Band VII	F <sub>tx</sub> = 2535 MHz, F <sub>int</sub> = 5190 MHz, F <sub>meas</sub> = 2655 MHz, Measure on all Pins		-123		dBm
<b>IMD3</b>	F <sub>tx</sub> = 20dBm; F <sub>int</sub> = -15dBm				
Band VIII	F <sub>tx</sub> = 897.5 MHz, F <sub>int</sub> = 852.5 MHz, F <sub>meas</sub> = 942.5 MHz, Measure on all Pins		-124		dBm
Band II	F <sub>tx</sub> = 1880 MHz, F <sub>int</sub> = 1800 MHz, F <sub>meas</sub> = 1960 MHz, Measure on all Pins		-126		dBm
Band VII	F <sub>tx</sub> = 2535 MHz, F <sub>int</sub> = 2415 MHz, F <sub>meas</sub> = 2655 MHz, Measure on all Pins		-125		dBm

\* See tuning schematic for 5000MHz to 6000MHz insertion loss

# QM12114

## SP4T RFFE GSM HIGH POWER SWITCH

PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNITS
<b>VSWR</b>					
RF1, RF2, RF3, RF4, RFCOM	698 MHz to 960 MHz		1.19		:1
RF1, RF2, RF3, RF4, RFCOM	1700 MHz to 2700 MHz		1.31		:1
RF1, RF2, RF3, RF4, RFCOM	3200 MHz to 3800 MHz		1.43		:1
RF1, RF2, RF3, RF4, RFCOM*	5000 MHz to 6000 MHz		1.60		:1

\* See tuning schematic for 5000MHz to 6000MHz insertion loss

### Isolation Matrix

Test conditions unless otherwise stated: all unused RF ports terminated in 50Ω, Input and Output = 50Ω, T = 25°C, V<sub>IO</sub> = 1.8V, SDATA/SCLK = 1.8 V / 0 V

SW STATE	INSERTION PORT	ISOLATION 698 – 960MHZ, TYPICAL (DB)			
		RF1	RF2	RF3	RF4
RF1	RF1		53	44	47
RF2	RF2	53		47	45
RF3	RF3	39	52		53
RF4	RF4	52	39	53	
RF1	RFCOM		46	40	40
RF2	RFCOM	47		40	40
RF3	RFCOM	47	46		40
RF4	RFCOM	47	46	40	

SW STATE	INSERTION PORT	ISOLATION 1710 – 2170MHZ, TYPICAL (DB)			
		RF1	RF2	RF3	RF4
RF1	RF1		39	33	37
RF2	RF2	39		37	33
RF3	RF3	31	40		38
RF4	RF4	39	31	38	
RF1	RFCOM		36	31	31
RF2	RFCOM	36		31	31
RF3	RFCOM	36	36		31
RF4	RFCOM	36	36	30	

## SP4T RFFE GSM HIGH POWER SWITCH

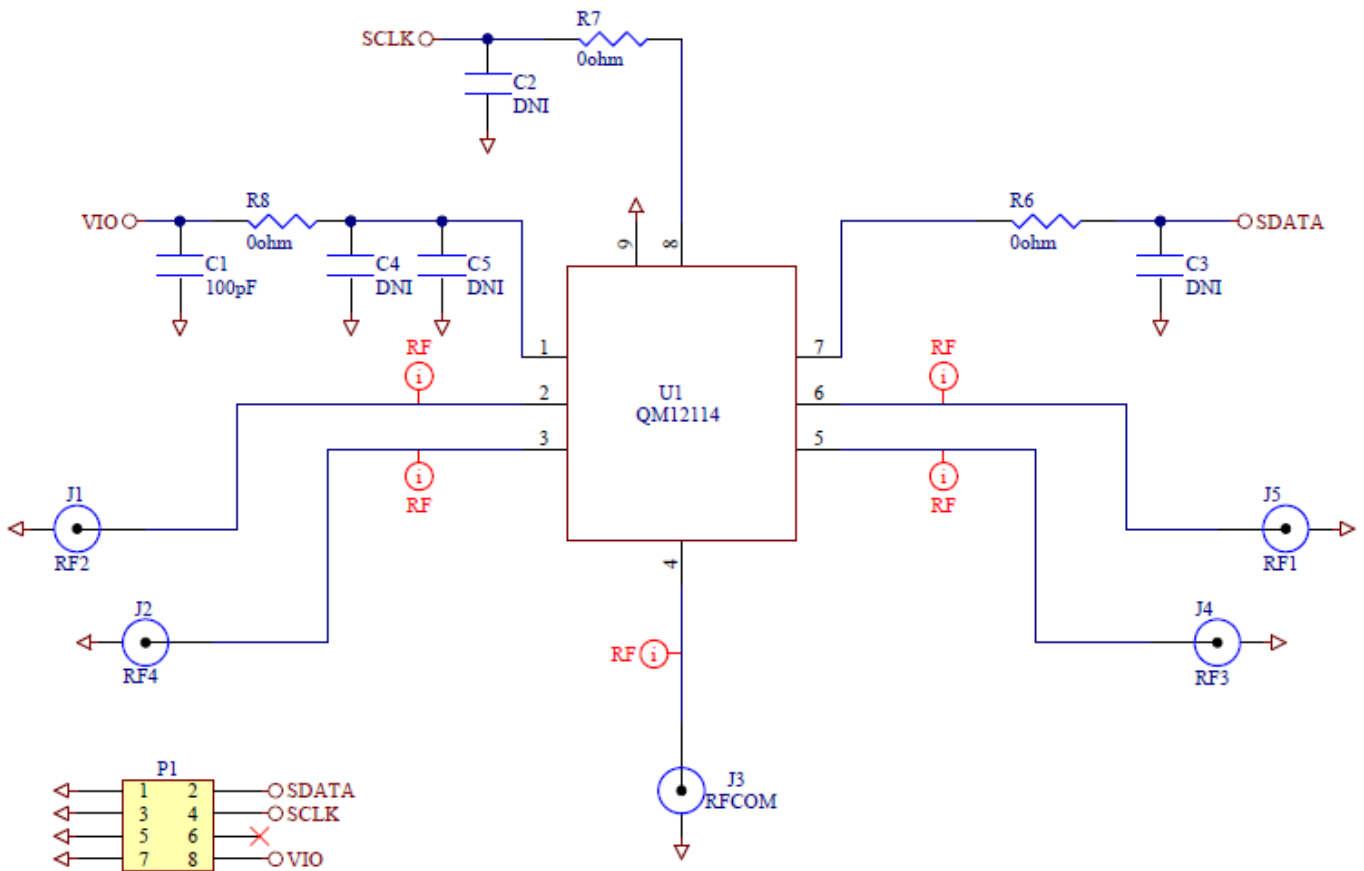
SW STATE	INSERTION PORT	ISOLATION 2300 – 2700MHZ, TYPICAL (DB)			
		RF1	RF2	RF3	RF4
RF1	RF1		36	30	34
RF2	RF2	35		33	30
RF3	RF3	28	36		34
RF4	RF4	35	28	34	
RF1	RFCOM		33	27	27
RF2	RFCOM	33		27	27
RF3	RFCOM	33	33		27
RF4	RFCOM	33	33	27	

SW STATE	INSERTION PORT	ISOLATION 3400 – 3800MHZ, TYPICAL (DB)			
		RF1	RF2	RF3	RF4
RF1	RF1		29	23	27
RF2	RF2	29		28	23
RF3	RF3	23	29		27
RF4	RF4	29	23	27	
RF1	RFCOM		28	23	23
RF2	RFCOM	27		23	23
RF3	RFCOM	27	28		23
RF4	RFCOM	27	28	23	

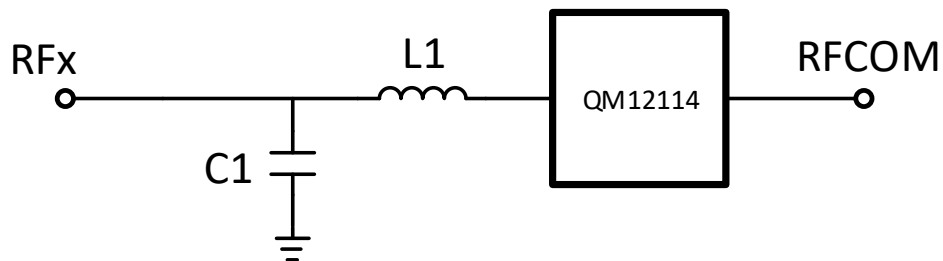
SW STATE	INSERTION PORT	ISOLATION 5000 – 6000MHZ, TYPICAL (DB)			
		RF1	RF2	RF3	RF4
RF1	RF1		22	16	23
RF2	RF2	22		22	17
RF3	RF3	17	22		20
RF4	RF4	22	18	20	
RF1	RFCOM		22	17	17
RF2	RFCOM	22		17	17
RF3	RFCOM	22	22		17
RF4	RFCOM	22	22	17	

# QM12114 SP4T RFFE GSM HIGH POWER SWITCH

## Application Circuit Schematic



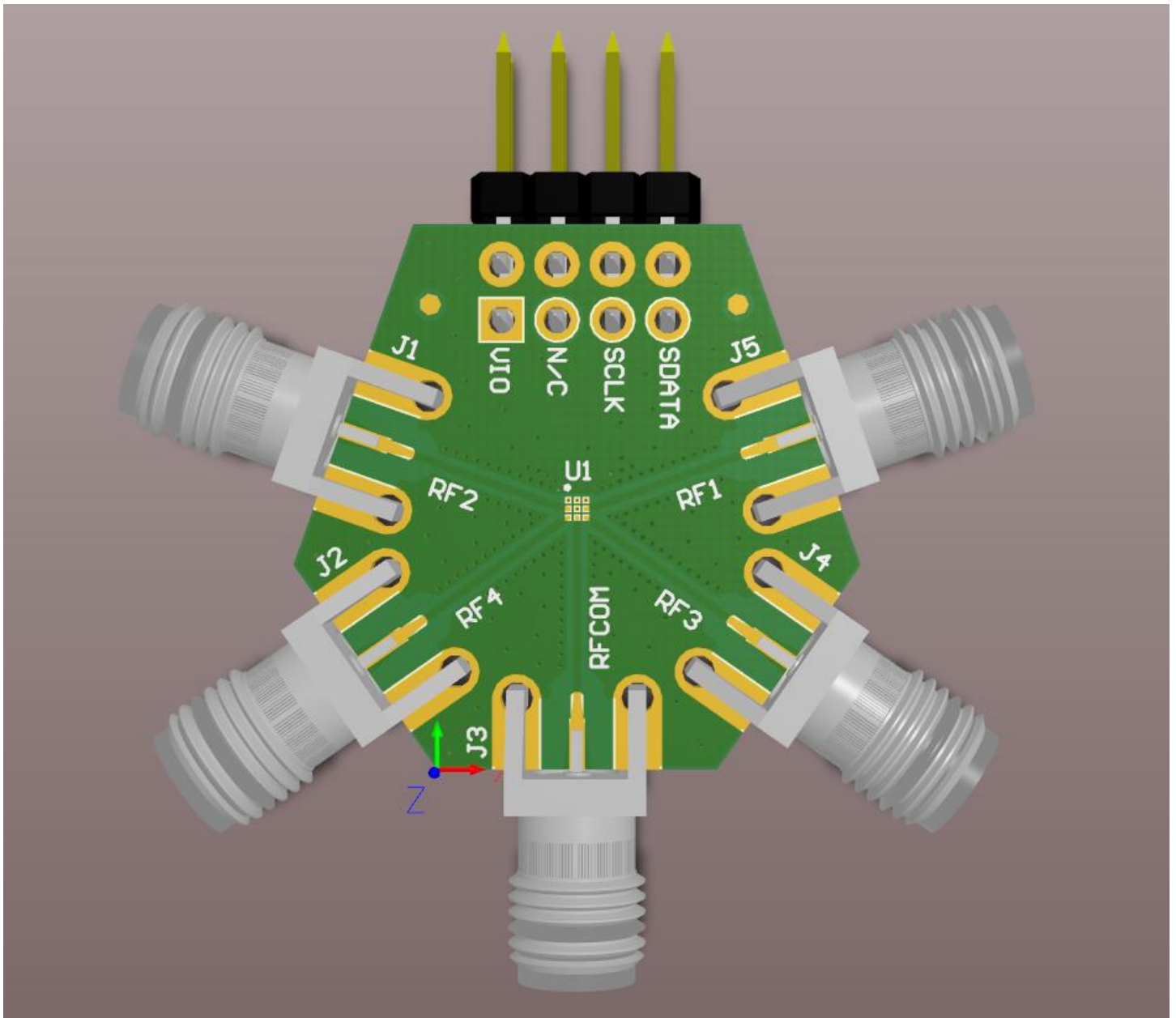
## Tuning Schematic for 500MHz – 600MHz



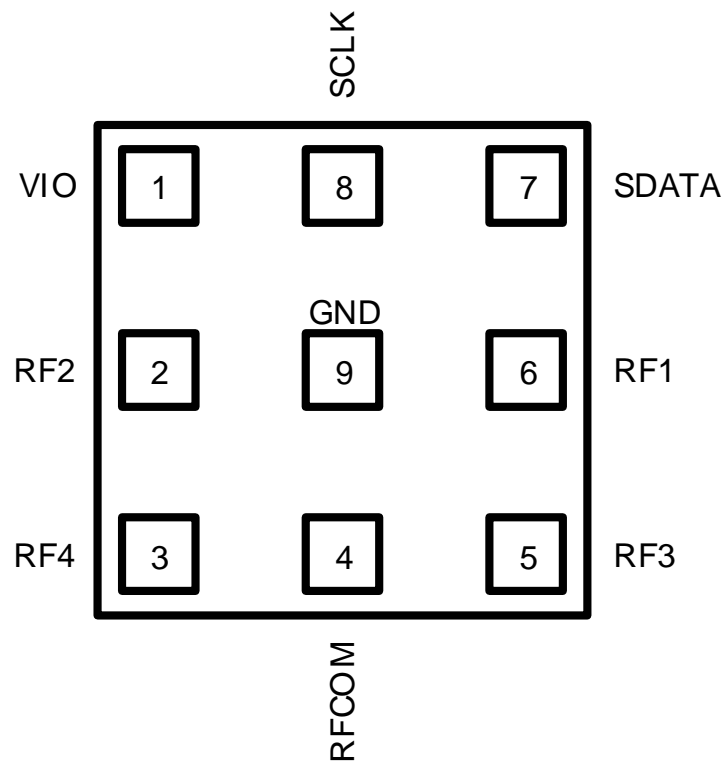
NAME	VALUE	PACKAGE	DESCRIPTION
C1	0.5pF	0201	Matching for optimized RF performance*
L1	1.5nH	0201	Matching for optimized RF performance*

\* Matching elements are subject to change based on specific system application

Evaluation Board Layout



## Pin Configuration and Description



Top View

PIN NO.	LABEL	DESCRIPTION
1	VIO	Voltage Supply
2	RF2	RF port
3	RF4	RF port
4	RFCOM	RF common port
5	RF3	RF port
6	RF1	RF port
7	SDATA	RFFE Data Signal
8	SCLK	RFFE Clock Signal
9	GND	Ground



## RFFE Register Map

### Register 0x0000 – SW\_CTRL0

Bit(s)	Field Name	Description	Reset	B/G	Trig	R/W
7:4	SPARE	Reserved for future use	0x0	No	0 - 2	R/W
3:0	SW_CTRL	0x00: Isolation 0x01: RF1 - RFC 0x02: RF2 - RFC 0x04: RF3 - RFC 0x08: RF4 - RFC	0x00	No	0-2	R/W

### Register 0x0001 – SPARE

Bit(s)	Field Name	Description	Reset	B/G	Trig	R/W
7:0	SPARE	Reserved for future use	0x00	No	0 - 2	R/W

### Register 0x001A – RFFE\_STATUS

Bit(s)	Field Name	Description	Reset	B/G	Trig	R/W
7	UDR_RST	Setting this bit initiates a software reset <i>Note: On software reset, this register and all User Defined registers (UDRs) are reset. This bit will always read as 0.</i>	0	No	No	W
6	CMD_FR_P_ERR	Command Frame received with a parity error	0	No	No	R/W
5	CMD_LEN_ERR	Command Sequence received with an incorrect length	0	No	No	R/W
4	ADDR_FR_P_ERR	Address Frame received with a parity error	0	No	No	R/W
3	DATA_FR_P_ERR	Data Frame received with a parity error	0	No	No	R/W
2	RD_INVLD_ADDR	Read Command Sequence received with an invalid address	0	No	No	R/W
1	WR_INVLD_ADDR	Write Command Sequence received with an invalid address	0	No	No	R/W
0	BID_GID_ERR	Read Command Sequence received with a BSID or GSID <i>Note: Reading this register resets this register.</i>	0	No	No	R/W

### Register 0x001B – GSID

Bit(s)	Field Name	Description	Reset	B/G	Trig	R/W
7:4	GSID0[3:0]	Group Slave ID0	0x0	No	No	R/W
3:0	GSID1[3:0]	Group Slave ID1	0x0	No	No	R/W

## Register 0x001C – PM\_TRIG

Bit(s)	Field Name	Description	Reset	B/G	Trig	R/W
7:6	PWR_MODE[1:0]	00: ACTIVE - Normal Operation 01: STARTUP - Reset all registers to default settings 10: ACTIVE - Low Power - Antenna in isolation 11: STARTUP - Reset all registers to default settings <i>Note: Setting PWR_MODE to STARTUP is identical to a hardware reset initiated by the VIO signal.</i>	0b10	B/G	No	R/W
5:3	TriggerMask[2:0]	Setting bit TriggerMask[N] disables Trigger[N] TriggerMask[N] updates <u>before</u> Trigger[N] is processed <i>Note: When Trigger[N] is disabled, writing to a register associated with Trigger[N] sends data directly to that register. If a register is associated with multiple triggers, then <u>all associated triggers</u> must be disabled to allow direct writes to the associated register.</i>	0b000	No	No	R/W
2:0	Trigger[2:0]	Setting bit Trigger[N] loads Trigger[N]'s associated registers <i>Note: When Trigger[N] is enabled, writing to a register associated with Trigger[N] sends data to that register's shadow. Setting the Trigger[N] bit loads data from shadow. <u>All triggers</u> are processed immediately and simultaneously and then cleared. Trigger[0], [1], and [2] will always read as 0.</i>	0b000	B/G	No	W

## Register 0x001D – PRODUCT\_ID

Bit(s)	Field Name	Description	Reset	B/G	Trig	R/W
7:0	PROD_ID[7:0]	Lower eight bits of Product Number <i>Note: These are read-only registers. However, as part of the special programming sequence for writing USID, a write command sequence is performed on one or both registers, but does not update them. See MIPI 6.6.2 for details.</i>	0x17	No	No	R

## Register 0x001E – MANUFACTURER\_ID

Bit(s)	Field Name	Description	Reset	B/G	Trig	R/W
7:0	MFG_ID[7:0]	Lower eight bits of MIPI Manufacturer ID <i>Note: These are read-only registers. However, as part of the special programming sequence for writing USID, a write command sequence is performed on one or both registers, but does not update them. See MIPI 6.6.2 for details.</i>	0x34	No	No	R

## SP4T RFFE GSM HIGH POWER SWITCH

## Register 0x001F – MAN\_USID

Bit(s)	Field Name	Description	Reset	B/G	Trig	R/W
7:6	RESERVED	Reserved for future use	0b00	No	No	R
		Upper two bits of MIPI Manufacturer ID				
5:4	MFG_ID[9:8]	<i>Note: This is a read-only register. However, as part of the special programming sequence for writing USID, a write command sequence is performed on this register, but does not update it. See MIPI 6.6.2 for details.</i>	0b01	No	No	R
		Programmable Unique Slave ID				
3:0	USID[3:0]	<i>Note: USID is only writeable using a special programming sequence. See MIPI 6.6.2 for details.</i>	0x8	No	No	R/W

## Register 0x0021 – REVISION\_ID

Bit(s)	Field Name	Description	Reset	B/G	Trig	R/W
7:6	MAJOR_REV[1:0]	Major Revisions - all layer	0b00	No	No	R
5:4	MINOR_REV[1:0]	Minor Revisions - metal only	0b00	No	No	R
3:0	MISC_REV[3:0]	Misc Revisions - mask variants	0b0001	No	No	R
		<i>Note: The REVISION_ID register contains this product's revision number which is set by Qorvo according to manufacture date. The value may change throughout the product life cycle.</i>				

## Power On and Off Sequence

It is very important that the user adheres to the correct timing sequences in order to avoid damaging the device. Figures are NOT drawn to scale.

1. Once VIO is powered down to 0V, wait a minimum of 10  $\mu$ s to reapply power to VIO. (see figure 1)

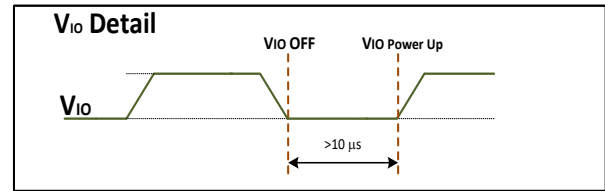


Figure 1 Digital Supply Detail

2. VIO must be applied for a minimum of 120 ns before sending SDATA/SCLK to ensure correct data transmission. (see figure 2)
3. VIO must be applied for a minimum of 15  $\mu$ s before applying RF power. (see figure 2)
4. Wait a minimum of 2.7 $\mu$ s after RFFE bus is idle to apply an RF signal. (see figure 2)

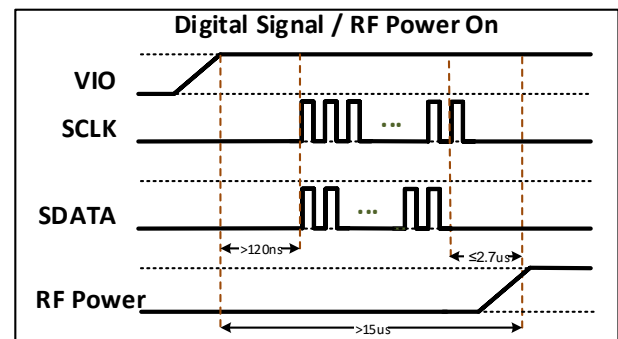


Figure 2 Digital Signal / RF Power-On Detail

5. RF power must not be applied during switching events. To ensure this, remove RF power before completing a register write that will change the switch mode. (see figure 3)

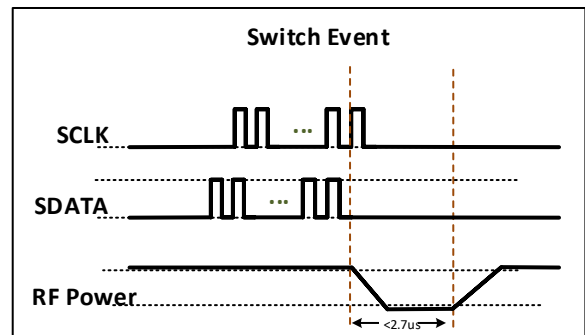


Figure 3 Switch Event Timing

6. If “Low Power Mode” is utilized, there must be a delay of 10  $\mu$ s before exiting “Low Power Mode”. (see figure 4)

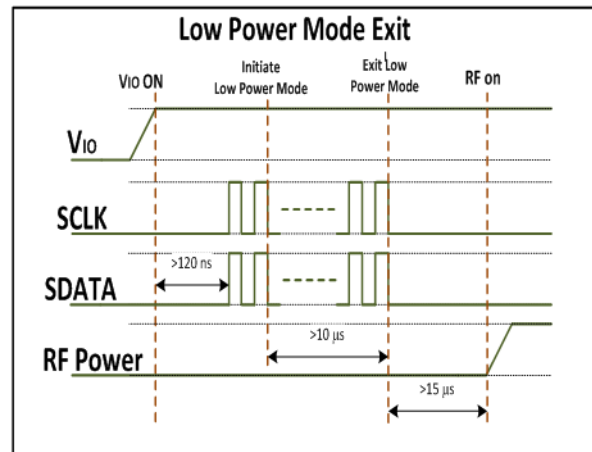


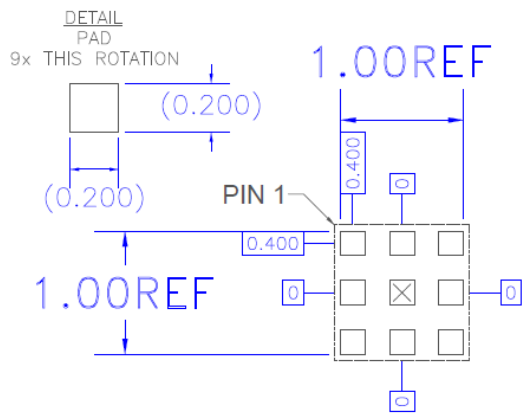
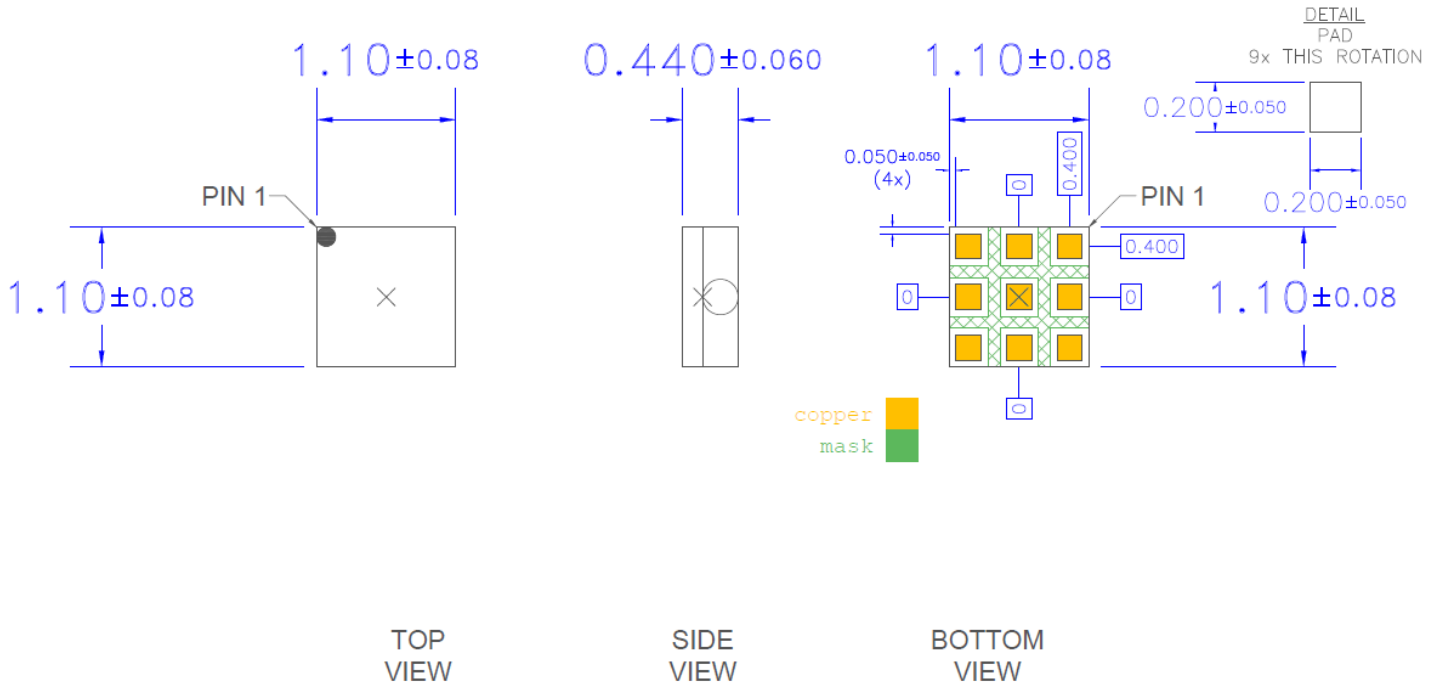
Figure 4 Low Power Mode Exit Timing

# QM12114

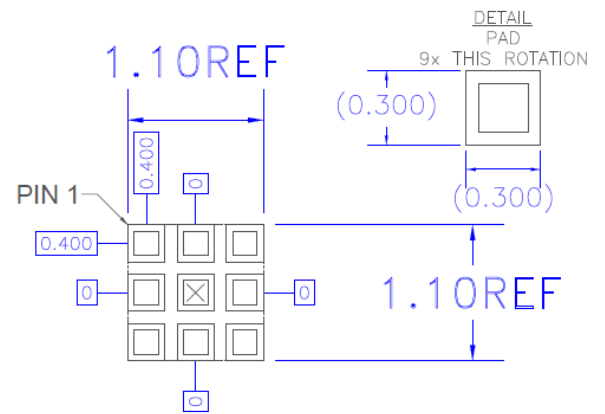
## SP4T RFFE GSM HIGH POWER SWITCH

### Mechanical Information

#### Package Drawing



RECOMMENDED  
LAND PATTERN



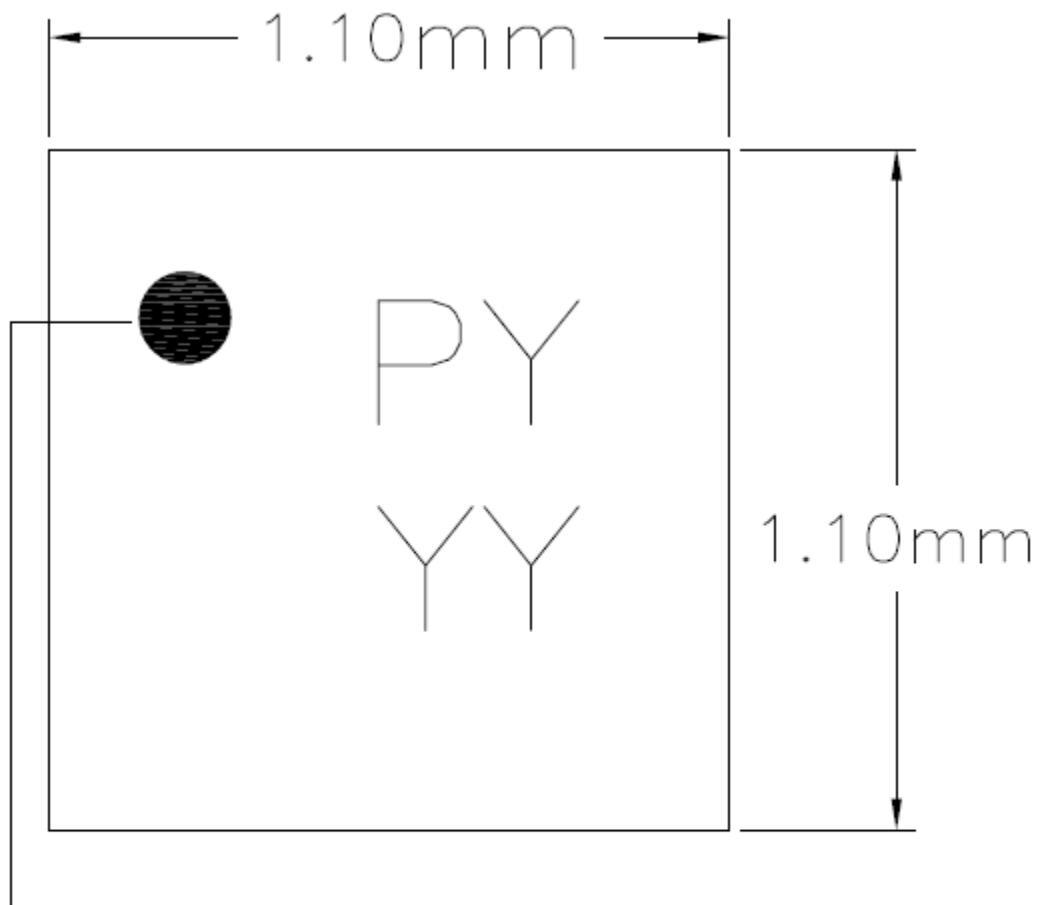
RECOMMENDED  
LAND PATTERN MASK

**Notes:**

1. All dimensions are in millimeters. Angles are in degrees.
2. Dimension and tolerance formats conform to ASME Y14.4M-1994.
3. The terminal #1 identifier and terminal numbering conform to JESD 95-1 SPP-012.

Branding Diagram

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Pin 1 Indicator

Trace Code to be assigned by SubCon

Where:

P is Product Code

YYY is Trace Code

# QM12114

## SP4T RFFE GSM HIGH POWER SWITCH

### Handling Precautions

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PARAMETER	RATING	STANDARD
ESD – Human Body Model (HBM)	Class 1C	ANSI/ESD/JEDEC JS-001
ESD – Charged Device Model (CDM)	Class C3	ANSI/ESDA/JEDEC JS-002
MSL – Moisture Sensitivity Level	Level 3	IPC/JEDEC J-STD-020



Caution!

ESD sensitive device

### Solderability

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Compatible with both lead-free (260 °C max. reflow temperature) and tin/lead (245 °C max. reflow temperature) soldering processes.

Package lead plating: Electrolytic plated Au over Ni

### RoHS Compliance

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This part is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>O<sub>2</sub>) Free
- SVHC Free





**QM12114**  
**SP4T RFFE GSM HIGH POWER SWITCH**

## Revision History

<b>Revision Code</b>	<b>Comments</b>
Rev A	Initial Production Release
Rev B	Update MSL Rating
Rev C	Added 6GHz data and tuning schematic, updated Mechanical Info drawings
Rev J	Corrected Package Drawing Dimension
Rev K	Update RFFE 2.0 compatible information
Rev L	Updated B13 2Fo Data
Rev M	Updated Switching Speed
Rev N	Updated Switching Speed wording, timing diagram, power handling
Rev O	Updated power handling
Rev P	Updated Branding Diagram